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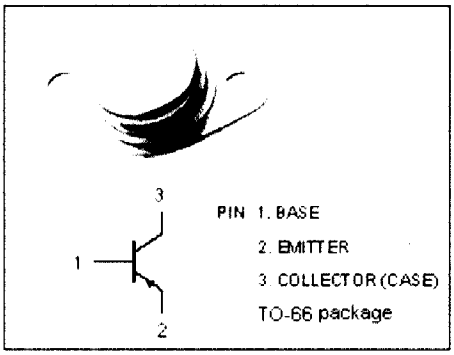
Silicon PNP Power Transistor

2SA766

DESCRIPTION

- Collector-Base Breakdown Voltage-
  : $V_{(BR)CBO}$= -150V(Min)
- High Collector Power Dissipation-
- Complement to Type 2SC1450

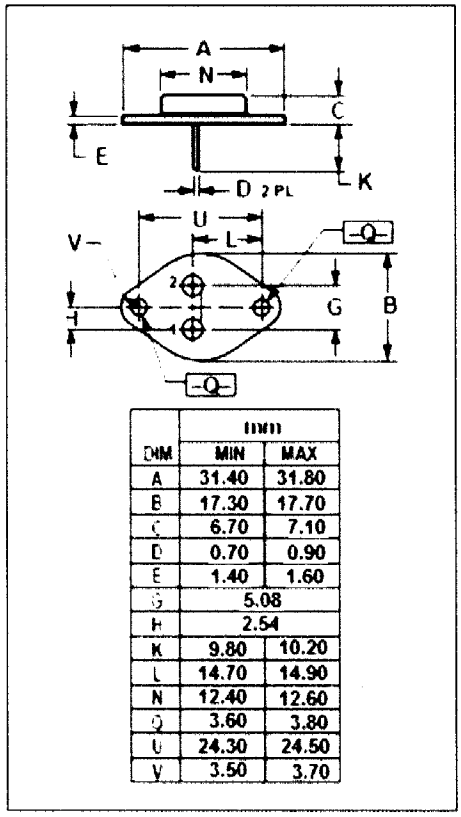


APPLICATIONS

- Line-operated vertical deflection output
- Medium power amplifier

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-150	V
V_{CEO}	Collector-Emitter Voltage	-150	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-0.4	A
I_{CM}	Collector Current-Peak	-1.2	A
P_C	Total Power Dissipation @ T_C=25℃	20	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-65~150	℃



DIM	mm MIN	MAX
A	31.40	31.80
B	17.30	17.70
C	6.70	7.10
D	0.70	0.90
E	1.40	1.60
G	5.08	
H	2.54	
K	9.80	10.20
L	14.70	14.90
N	12.40	12.60
Q	3.60	3.80
U	24.30	24.50
V	3.50	3.70

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CER}$	Collector-Emitter Breakdown Voltage	I_C= -0.2A; L= 25mH, R_{BE}= 5kΩ	-150			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= -1mA; I_C= 0	-5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -1A; I_B= -0.1A			-1.0	V
$V_{BE(on)-1}$	Base-Emitter On Voltage	I_C= -0.1A; V_{CE}= -5V			-0.8	V
$V_{BE(on)-2}$	Base-Emitter On Voltage	I_C= -0.5A; V_{CE}= -5V			-1.0	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -60V; I_E= 0			-30	μ A
h_{FE-1}	DC Current Gain	I_C= -0.1A; V_{CE}= -5V	35		150	
h_{FE-2}	DC Current Gain	I_C= -0.5A; V_{CE}= -5V	35			
f_T	Current-Gain—Bandwidth Product	I_E= 0.1A; V_{CB}= -10V		15		MHz